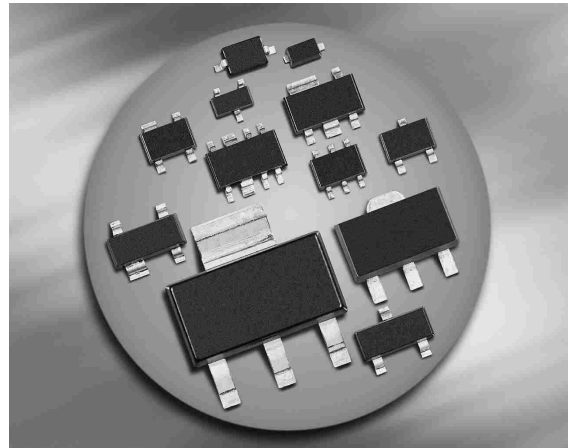


**BCR133../SEM11**

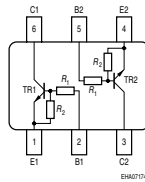
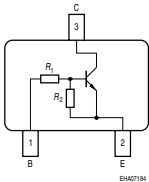
**PNP TY Digital Transistor**

- Switching in circuit, inverter, interface circuit, drive circuit
- Built in bias resistor ( $R_1 = 10\text{ k}\Omega$ ,  $R_2 = 10\text{ k}\Omega$ )
- For 6-PIN packages: two (galvanic) internal isolated transistors with good matching in one package



**BCR133/F/L3**  
**BCR133T/W**

**BCR133S/U**  
**SEM11**



Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR133	WCs	1=B	2=E	3=C	-	-	-	SOT23
BCR133F	WCs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR133L3	WC	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR133S	WCs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR133T	WCs	1=B	2=E	3=C	-	-	-	SC75
BCR133U	WCs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74
BCR133W	WC	1=B	2=E	3=C	-	-	-	SOT323
SEM11	WC	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT666

## BCR133../SEMH11

## Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Emitter-base voltage	$V_{EBO}$	10	
Input on voltage	$V_{i(on)}$	20	
Collector current	$I_C$	100	mA
Total power dissipation- BCR133, $T_S \leq 102^\circ\text{C}$ BCR133F, $T_S \leq 128^\circ\text{C}$ BCR133L3, $T_S \leq 135^\circ\text{C}$ BCR133S, $T_S \leq 115^\circ\text{C}$ BCR133T, $T_S \leq 109^\circ\text{C}$ BCR133U, $T_S \leq 118^\circ\text{C}$ BCR133W, $T_S \leq 124^\circ\text{C}$ SEMH11, $T_S \leq 75^\circ\text{C}$	$P_{tot}$	200 250 250 250 250 250 250 250	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

## Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$		K/W
BCR133		$\leq 240$	
BCR133F		$\leq 90$	
BCR133L3		$\leq 60$	
BCR133S		$\leq 140$	
BCR133T		$\leq 165$	
BCR133U		$\leq 133$	
BCR133W SEMH11		$\leq 105$ $\leq 300$	

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**BCR133.../SEM11**
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	0.75	mA
DC current gain <sup>1)</sup> $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{FE}$	30	-	-	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	$V_{CEsat}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.8	-	1.5	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	1	-	2.5	
Input resistor	$R_1$	7	10	13	k $\Omega$
Resistor ratio	$R_1/R_2$	0.9	1	1.1	-
<b>AC Characteristics</b>					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	130	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	3	-	pF

<sup>1)</sup>Pulse test:  $t < 300 \mu\text{s}; D < 2\%$